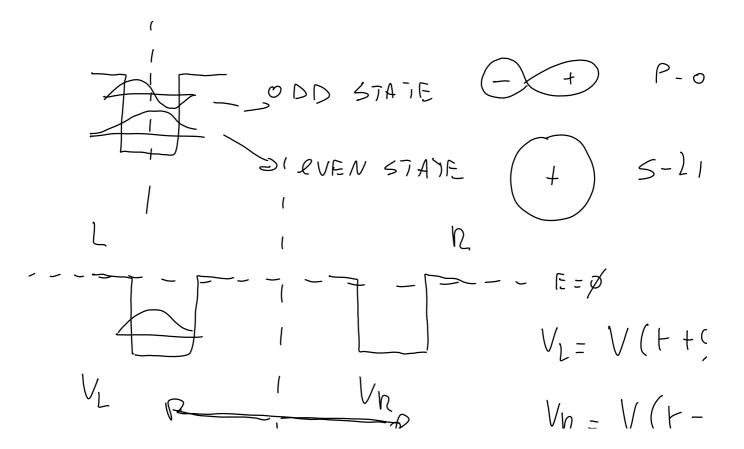
Linear Combination of Atomic Orbitals

- "You don't understand any electronic structure property if you can't explain it in a 2x2 (matrix) problem" Manuel Cardona
- •Linear combination of atomic orbitals: the LCAO approximation
- •Formation of bonding and anti-bonding levels: on-site and overlap integrals
- ·Löwdin orthogonalization of atomic wavefunctions
- Matrix formalism of the Schrödinger equation
- •Example: energy level of three coupled quantum wells

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$$(T+V) \phi = \varepsilon_s \phi_s$$

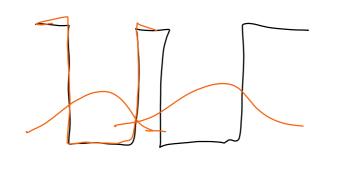
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SOLUTION - DY = QL
$$\phi_L = \phi_S(\tau + \frac{Q}{Z}) + \frac{Q}{Z}$$

$$\int \phi_{L}^{*} \left[\left(T + V_{L} + V_{R}\right) \left(O_{L} \phi_{L} + O_{R} \phi_{R}\right) \right] dn = \int e^{-\frac{\pi}{2}} \left[\left(T + V_{L} + V_{R}\right) \left(O_{L} \phi_{L} + O_{R} \phi_{R}\right) \right] dn = \int e^{-\frac{\pi}{2}} \left[\left(T + V_{L} + V_{R}\right) \left(O_{L} \phi_{L} + O_{R} \phi_{R}\right) \right] dn = \int e^{-\frac{\pi}{2}} \left[\left(T + V_{L} + V_{R}\right) \left(O_{L} \phi_{L} + O_{R} \phi_{R}\right) \right] dn = \int e^{-\frac{\pi}{2}} \left[\left(T + V_{L} + V_{R}\right) \left(O_{L} \phi_{L} + O_{R} \phi_{R}\right) \right] dn = \int e^{-\frac{\pi}{2}} \left[\left(T + V_{L} + V_{R}\right) \left(O_{L} \phi_{L} + O_{R} \phi_{R}\right) \right] dn = \int e^{-\frac{\pi}{2}} \left[\left(T + V_{L} + V_{R}\right) \left(O_{L} \phi_{L} + O_{R} \phi_{R}\right) \right] dn = \int e^{-\frac{\pi}{2}} \left[\left(T + V_{L} + V_{R}\right) \left(O_{L} \phi_{L} + O_{R} \phi_{R}\right) \right] dn = \int e^{-\frac{\pi}{2}} \left[\left(T + V_{L} + V_{R}\right) \left(O_{L} \phi_{L} + O_{R} \phi_{R}\right) \right] dn = \int e^{-\frac{\pi}{2}} \left[\left(T + V_{L} + V_{R}\right) \left(O_{L} \phi_{L} + O_{R} \phi_{R}\right) \right] dn = \int e^{-\frac{\pi}{2}} \left[\left(T + V_{L} + V_{R}\right) \left(O_{L} \phi_{L} + O_{R} \phi_{R}\right) \right] dn = \int e^{-\frac{\pi}{2}} \left[\left(T + V_{L} + V_{R}\right) \left(O_{L} \phi_{L} + O_{R} \phi_{R}\right) \right] dn = \int e^{-\frac{\pi}{2}} \left[\left(T + V_{L} + V_{R}\right) \left(O_{L} \phi_{L} + O_{R} \phi_{R}\right) \right] dn = \int e^{-\frac{\pi}{2}} \left[\left(T + V_{L} + V_{R}\right) \left(O_{L} \phi_{L} + O_{R} \phi_{R}\right) \right] dn = \int e^{-\frac{\pi}{2}} \left[\left(T + V_{L} + V_{R}\right) \left(O_{L} \phi_{L} + O_{R} \phi_{R}\right) \right] dn = \int e^{-\frac{\pi}{2}} \left[\left(T + V_{L} + V_{R}\right) \left(O_{L} \phi_{L} + O_{R} \phi_{R}\right) \right] dn = \int e^{-\frac{\pi}{2}} \left[\left(T + V_{L} + V_{R}\right) \left(O_{L} \phi_{L} + O_{R} \phi_{R}\right) \right] dn = \int e^{-\frac{\pi}{2}} \left[\left(T + V_{L} + V_{R}\right) \left(O_{L} \phi_{L} + O_{R} \phi_{R}\right) \right] dn = \int e^{-\frac{\pi}{2}} \left[\left(T + V_{L} + V_{R}\right) \left(O_{L} \phi_{L} + O_{R} \phi_{R}\right) \right] dn = \int e^{-\frac{\pi}{2}} \left[\left(T + V_{L} + V_{R}\right) \left(O_{L} \phi_{L} + O_{R} \phi_{R}\right) \right] dn = \int e^{-\frac{\pi}{2}} \left[\left(T + V_{L} + V_{R}\right) \left(O_{L} \phi_{L} + O_{R} \phi_{R}\right) \right] dn = \int e^{-\frac{\pi}{2}} \left[\left(T + V_{L} + V_{R}\right) \left(O_{L} \phi_{L} + O_{R} \phi_{R}\right) \right] dn = \int e^{-\frac{\pi}{2}} \left[\left(T + V_{L} + V_{R}\right) \left(O_{L} \phi_{L} + O_{R} \phi_{R}\right) \right] dn = \int e^{-\frac{\pi}{2}} \left[\left(T + V_{L} + V_{R}\right) \left(O_{L} \phi_{L} + O_{R} \phi_{R}\right) \right] dn = \int e^{-\frac{\pi}{2}} \left[\left(T + V_{L} + V_{R}\right) \left(O_{L} \phi_{L} + O_{R} \phi_{R}\right) \right] dn = \int e^{-\frac{\pi}{2}} \left[\left(T + V_{L} + V_{R}\right) \left(O_{L} \phi_{L} + O_{R} \phi_{R}\right) \right] dn = \int e^{-\frac{\pi}{2}} \left[\left$$

$$(3) < \phi_L / + v_n / o_n \phi_n) = o_n < \phi_L / \varepsilon_s / \phi_n$$

$$(9) < \alpha_L | V_L | \alpha_n | \phi_n \rangle = O_n < \alpha_L | V_L | \phi_n \rangle$$



$$\langle \phi_L | E | e_L \phi_L + e_n \phi_n \rangle = o_{i_L} E \langle \phi_L | i$$

$$Q_{L} \mathcal{E}_{S} - Q_{L} \mathcal{B} + Q_{R} \mathcal{E} \mathcal{F} - Q_{R} \mathcal{F} = Q_{L} \mathcal{E} + Q_{R} \mathcal{E}$$

$$\begin{cases} Q_{L} (\mathcal{E} - \mathcal{B}) + Q_{R} (\mathcal{E} - \mathcal{B}) = \mathcal{E} Q_{L} + Q_{R} \mathcal{E} \\ Q_{L} (\mathcal{A} \mathcal{E} - \mathcal{B}) + Q_{R} (\mathcal{E} - \mathcal{B}) = \mathcal{E} Q_{L} + Q_{L} \mathcal{E} \\ \mathcal{E} - \mathcal{G} \mathcal{E} \mathcal{E} - \mathcal{G} \mathcal{E}$$

EIGEN VALVE ENFRGY E

det
$$\begin{vmatrix} \xi - \beta - \xi \\ -\gamma & \xi - \beta - \xi \end{vmatrix} = \emptyset$$

$$(\xi - \beta - \xi)^2 - \gamma^2 = \emptyset \quad \xi - \beta - \xi = \pm 1$$

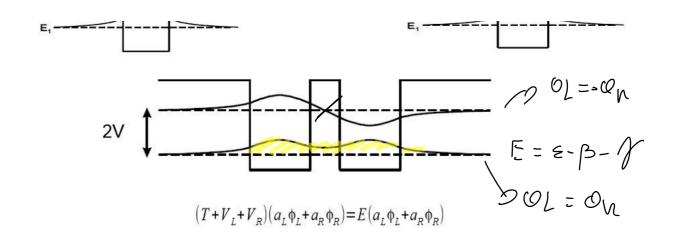
$$\xi = \xi - \beta + \gamma$$

$$|\xi - \beta| = 0$$

Linear combination of atomic orbitals - LCAO

In the LCAO approximation the problem of two interacting atoms (left and right) is solved by expressing the solution as a linear combination of the eigenfunction solving the single atom problem.

$$(T+V_L)\phi_L = E_s\phi_L \qquad (T+V_R)\phi_R = E_s\phi_R$$

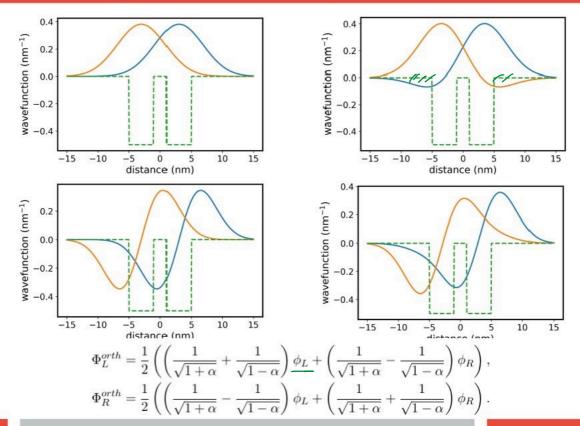


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Löwdin orthogonalization of s and p orbitals



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Secular matrix for the LCAO approximation

$$-\beta = \langle \phi_L | V_R | \phi_L \rangle$$
 On-site integral

$$-\gamma = \langle \phi_L | V_L | \phi_R \rangle$$
 Off-site or overlap integral

Setting det=0 we obtain the energies of the bonding and anti-bonding levels

$$E = \epsilon - \beta \pm \gamma$$

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Matrix formalism

2 QWs Hamiltonian

$$H = T + V_L + V_R$$

2 QWs Schrödinger equation $H(a_L \phi_L + a_R \phi_R) = E(a_L \phi_L + a_R \phi_R)$

Schrödinger equation in matrix formalism

$$\begin{bmatrix} \langle \phi_{L}|H|\phi_{L} \rangle & \langle \phi_{L}|H|\phi_{R} \rangle \\ \langle \phi_{R}|H|\phi_{L} \rangle & \langle \phi_{R}|H|\phi_{R} \rangle \end{bmatrix} \begin{bmatrix} a_{L} \\ a_{R} \end{bmatrix} = E \begin{bmatrix} a_{L} \\ a_{R} \end{bmatrix}$$

Secular determinant

$$det \begin{bmatrix} \langle \phi_{L}|H|\phi_{L}\rangle - E & \langle \phi_{L}|H|\phi_{R}\rangle \\ \langle \phi_{R}|H|\phi_{L}\rangle & \langle \phi_{R}|H|\phi_{R}\rangle - E \end{bmatrix} = 0$$

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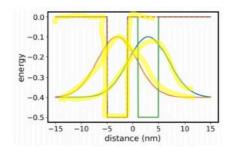
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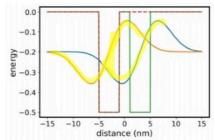
Overlap integral

Overlap integral properties

- γ gets larger as the distance between the 2 QW is reduces
- $\gamma > 0$ for even (s-type) orbitals

- y < 0 for odd (p-type) orbitals
- $|\gamma_s| > |\gamma_p|$ due to a better orbital overlap



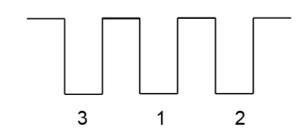


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Three coupled QW



Assuming only near-neighbour interaction and setting all the on-site integral to zero

$$E_1 = \epsilon - \sqrt{2} \gamma$$

$$|\Phi_2| - \gamma$$

$$\epsilon - E$$

$$E_2 = \epsilon$$

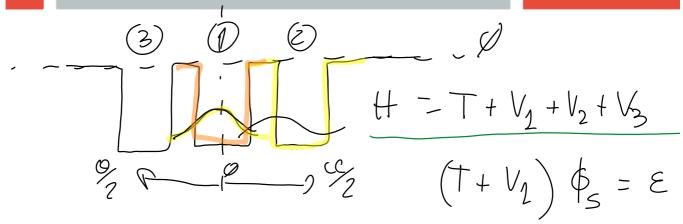
$$|\Phi_3|$$
 $-\gamma$

$$\epsilon - E$$

$$E_3 = \epsilon + \sqrt{2} \gamma$$

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$$\psi = Q_1 + Q_2 + Q_3 + Q_3$$

 $\phi_2 = \phi_1$

LOWDIN METHOD

 $\phi_3 = \phi_1$

. Mear neighbour htoraction

· B on-site integral 2 \$

(\$2, -p) = 2-B

 $\langle \phi_{2} | H | \phi_{2} \rangle = \langle \phi_{2} | T + V_{2} | \phi_{1} \rangle + \langle \phi_{1} | V_{2} | \phi_{1}$

$$= -\beta$$

$$\langle \phi_2 | H + \phi_2 \rangle = \langle \phi_2 | V_1 | \phi_2 \rangle + \langle \phi_2 | T + V_2 | \phi_2$$

$$-\gamma = \frac{1}{2} \left(\frac{1}{4}\right)$$

Bad

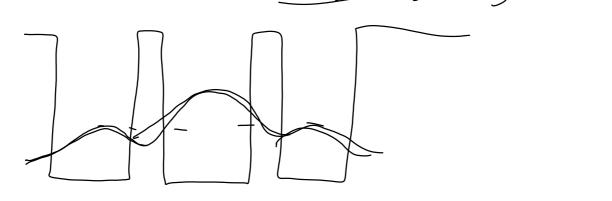
$$(\varepsilon - E)^3 - 2 \eta^2 (\varepsilon - E) = \emptyset$$

$$(\xi - E) ((\xi - E)^2 - 2 / 2) = \emptyset$$
 $E = 0$

820

$$\begin{bmatrix} 2 & -N & -N \\ -N & 2 & 0 \\ -N & 0 & E \end{bmatrix} \begin{bmatrix} Q_1 \\ Q_2 \\ G_3 \end{bmatrix} = \begin{bmatrix} Q_1 \\ Q_2 \\ Q_3 \end{bmatrix}$$

$$E = E - \sqrt{2}$$
 $Q_2 = Q_3$ $Q_1 = \sqrt{2}$ $Q_2 = Q_3$ $Q_2 = \sqrt{2}$ $Q_2 = \sqrt{2}$ $Q_3 = \sqrt{2}$



$$E = e$$

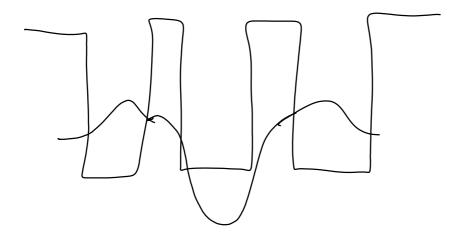
$$Q_2 = -Q_2$$

$$Q_1 = \emptyset$$

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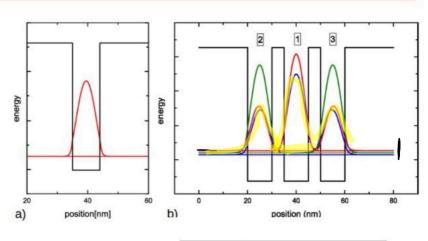
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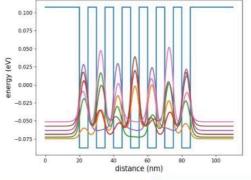


Three coupled QW

Squared wavefunctions for one, three and seven coupled quantum wells



As the number of interacting QWs increases more and more levels are obtained. In the limit of infinite levels a "continuum" band is formed. This is true also if we consider only nearneighbour interaction.



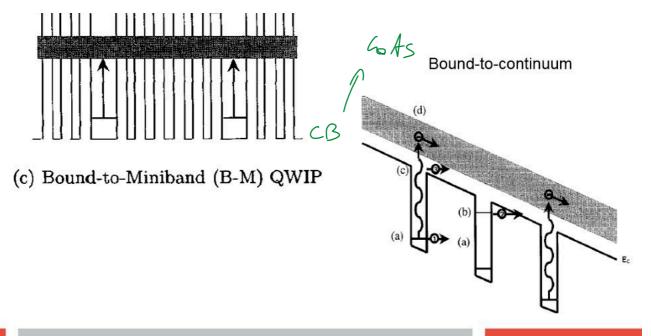
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Application to intersubband photodetectors

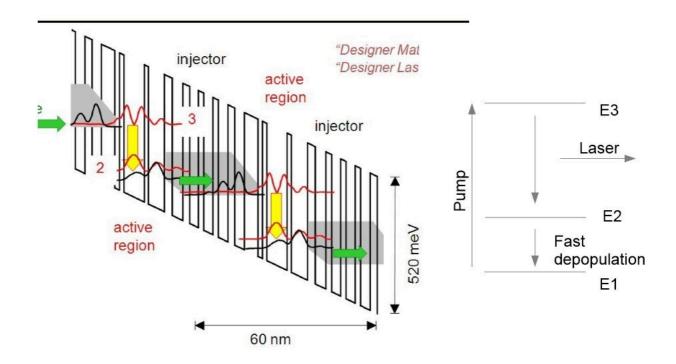
Far-infrared photodetectors exploiting intersubband transitions



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Another application: the quantum cascade laser



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